

PATENT COOPERATION TREATY

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From the INTERNATIONAL BUREAU

PCTNOTIFICATION CONCERNING
SUBMISSION OR TRANSMITTAL
OF PRIORITY DOCUMENT

(PCT Administrative Instructions, Section 411)

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Applicant NEC CORPORATION et al	

- By means of this Form, which replaces any previously issued notification concerning submission or transmittal of priority documents, the applicant is hereby notified of the date of receipt by the International Bureau of the priority document(s) relating to all earlier application(s) whose priority is claimed. Unless otherwise indicated by the letters "NR", in the right-hand column or by an asterisk appearing next to a date of receipt, the priority document concerned was submitted or transmitted to the International Bureau in compliance with Rule 17.1(a) or (b).
- (If applicable) The letters "NR" appearing in the right-hand column denote a priority document which, on the date of mailing of this Form, had not yet been received by the International Bureau under Rule 17.1(a) or (b). Where, under Rule 17.1(a), the priority document must be submitted by the applicant to the receiving Office or the International Bureau, but the applicant fails to submit the priority document within the applicable time limit under that Rule, the attention of the applicant is directed to Rule 17.1(c) which provides that no designated Office may disregard the priority claim concerned before giving the applicant an opportunity, upon entry into the national phase, to furnish the priority document within a time limit which is reasonable under the circumstances.
- (If applicable) An asterisk (*) appearing next to a date of receipt, in the right-hand column, denotes a priority document submitted or transmitted to the International Bureau but not in compliance with Rule 17.1(a) or (b) (the priority document was received after the time limit prescribed in Rule 17.1(a) or the request to prepare and transmit the priority document was not submitted to the receiving Office after the applicable time limit under Rule 17.1(b)). Even though the priority document was not furnished in compliance with Rule 17.1(a) or (b), the International Bureau will nevertheless transmit a copy of the document to the designated Offices, for their consideration. In case such a copy is not accepted by the designated Office as the priority document, Rule 17.1(c) provides that no designated Office may disregard the priority claim concerned before giving the applicant an opportunity, upon entry into the national phase, to furnish the priority document within a time limit which is reasonable under the circumstances.

Priority date	Priority application No.	Country or regional Office or PCT receiving Office	Date of receipt of priority document
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CLAIMS

1. (Amended) A microstrip line having at least a dielectric layer and a conductor layer disposed in order on a first electrode layer, said microstrip line
5 characterized in that said dielectric layer is formed by oxidizing, nitriding, or oxynitriding said first electrode layer, and said conductor layer comprises at least conductive nanoparticles and a binder resin.
2. A microstrip line according to claim 1, characterized in that said
10 conductive nanoparticles contain at least one of gold, silver, copper, silver oxide, copper oxide, tin oxide, zinc oxide, and indium oxide, an average particle diameter of said conductive nanoparticles is 1nm or more and 500nm or less, and the content of said conductive nanoparticles in said conductor layer is 10wt% or more and less than 100wt%.
- 15 3. A microstrip line according to claim 1 or 2, characterized in that a characteristic impedance is 1 Ω or less.
4. A microstrip line according to claim 1 or 2, characterized in that a
20 second electrode layer is disposed on said conductor layer.
5. A method of fabricating the microstrip line according to claim 1 or 2, characterized by forming said conductor layer on said first electrode layer and forming said dielectric layer between said first electrode layer and said
25 conductor layer by carrying out heat treatment at a temperature of 250°C or more and 600°C or less.
6. A method of fabricating the microstrip line according to claim 5,

characterized in that said dielectric layer is formed by oxidizing, nitriding, or oxynitriding said first electrode layer.